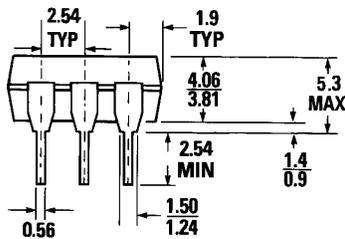
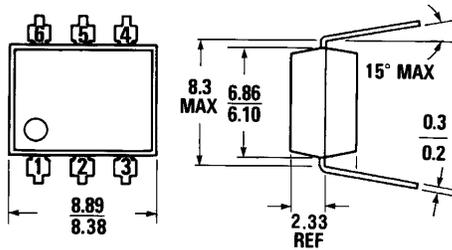


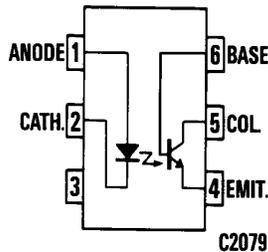
**CNY17-1 CNY17-3  
CNY17-2 CNY17-4**

**PACKAGE DIMENSIONS**



0.40 DIMENSIONS IN mm  
PACKAGE CODE K

ST1603A



Equivalent Circuit

**DESCRIPTION**

The CNY17 series consists of a Gallium Arsenide IRED coupled with an NPN phototransistor.

**FEATURES**

- High isolation voltage  
5300 VAC RMS—1 minute  
7500 VAC PEAK—1 minute
- High  $BV_{CEO}$  minimum 70 volts
- Current transfer ratio in selected groups:  
CNY17-1: 40%- 80%  
CNY17-2: 63%-125%  
CNY17-3: 100%-200%  
CNY17-4: 160%-320%
- Maximum switching time in saturation specified
- Underwriters Laboratory (UL) recognized File #E90700

**APPLICATIONS**

- Power supply regulators
- Digital logic inputs
- Microprocessor inputs
- Appliance sensor systems
- Industrial controls

**ABSOLUTE MAXIMUM RATINGS**

**TOTAL PACKAGE**

Storage temperature .....	-55°C to 150°C
Operating temperature .....	-55°C to 100°C
Lead temperature (soldering, 10 sec) .....	260°C
Total package power dissipation @ 25°C (LED plus detector) .....	260 mW
Derate linearly from 25°C .....	3.5 mW/°C

**INPUT DIODE**

Forward DC current .....	90 mA
Reverse voltage .....	6 V
Peak forward current (1 $\mu$ s pulse, 300 pps) .....	3.0 A
Power dissipation 25°C ambient .....	135 mW
Derate linearly from 25°C .....	1.8 mW/°C

**OUTPUT TRANSISTOR**

Power dissipation @ 25°C .....	200 mW
Derate linearly from 25°C .....	2.67 mW/°C

**ELECTRO-OPTICAL CHARACTERISTICS** (25°C Temperature Unless Otherwise Specified)

<b>INDIVIDUAL COMPONENT CHARACTERISTICS</b>						
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
<b>INPUT DIODE</b>						
Forward voltage	$V_f$		1.3	1.50	V	$I_f=60\text{ mA}$
Forward voltage temp. coefficient	$\frac{\Delta V_f}{\Delta T_A}$		-1.8		mV/°C	
Reverse voltage	$V_R$	6.0	15		V	$I_R=10\ \mu\text{A}$
Junction capacitance	$C_j$		50		pF	$V_f=0\text{ V}, f=1\text{ MHz}$
			65		pF	$V_f=1\text{ V}, f=1\text{ MHz}$
Reverse leakage current	$I_R$		.35	10	$\mu\text{A}$	$V_R=3.0\text{ V}$
<b>OUTPUT TRANSISTOR</b>						
DC forward current gain	$h_{FE}$	100	500			$V_{CE}=5\text{ V}, I_C=100\ \mu\text{A}$
Breakdown voltage Collector to emitter	$BV_{CE0}$	70			V	$I_C=10\text{ mA}, I_E=0$

**ELECTRO-OPTICAL CHARACTERISTICS**  
(25°C Temperature Unless Otherwise Specified) (Cont'd)

**TRANSFER CHARACTERISTICS** (Cont'd)

AC CHARACTERISTICS	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
<b>SATURATED SWITCHING TIMES</b>						
Turn-on time	$t_{on}$					
CNY17-1			3.0	5.5	$\mu$ S	$I_F = 20$ mA, $V_{CE} = 0.4$ V
CNY17-2, CNY17-3, CNY17-4			4.2	8.0	$\mu$ S	$I_F = 10$ mA, $V_{CE} = 0.4$ V
Rise-time	$t_r$					
CNY17-1			2.0	4.0	$\mu$ S	$I_F = 20$ mA, $V_{CE} = 0.4$ V
CNY17-2, CNY17-3, CNY17-4			3.0	6.0	$\mu$ S	$I_F = 10$ mA, $V_{CE} = 0.4$ V
Turn-off time	$t_{off}$					
CNY17-1			18	34	$\mu$ S	$I_F = 20$ mA, $V_{CE} = 0.4$ V
CNY17-2, CNY17-3, CNY17-4			23	39	$\mu$ S	$I_F = 10$ mA, $V_{CE} = 0.4$ V
Fall-time	$t_f$					
CNY17-1			11	20	$\mu$ S	$I_F = 20$ mA, $V_{CE} = 0.4$ V
CNY17-2, CNY17-3, CNY17-4			14	24	$\mu$ S	$I_F = 10$ mA, $V_{CE} = 0.4$ V

**ISOLATION CHARACTERISTICS**

CHARACTERISTICS	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
Isolation Voltage	$V_{iso}$	5300			$V_{AC}$ RMS	$I_{i,o} \leq 1$ $\mu$ A, 1 minute
	$V_{iso}$	7500			$V_{AC}$ PEAK	$I_{i,o} \leq 1$ $\mu$ A, 1 minute
Isolation resistance	$R_{iso}$	$10^{11}$			ohms	$V_{i,o} = 500$ VDC
Isolation capacitance	$C_{iso}$		0.5		pF	$f = 1$ MHz

**ELECTRICAL CHARACTERISTIC CURVES**  
(25°C Free Air Temperature Unless Otherwise Specified)

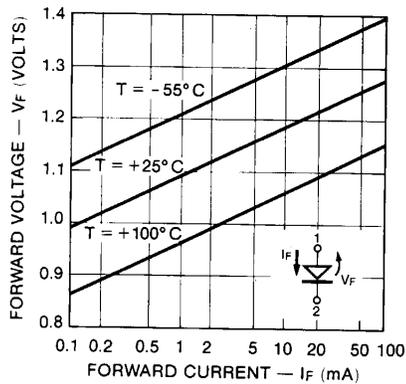


Fig. 1. Forward Voltage vs. Current

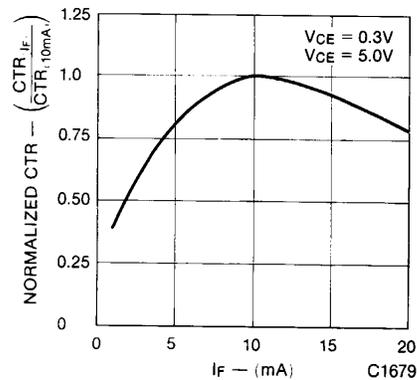
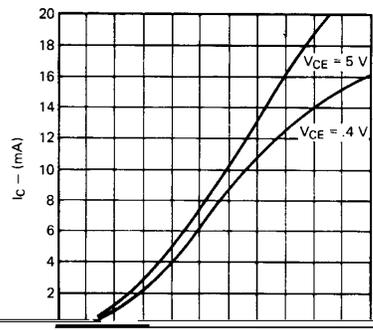
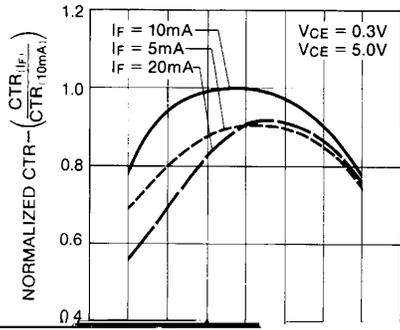


Fig. 2. Normalized CTR vs. Forward Current

**ELECTRICAL CHARACTERISTIC CURVES**

(25°C Free Air Temperature Unless Otherwise Specified) (Cont'd)



**ELECTRICAL CHARACTERISTIC CURVES**  
(25°C Free Air Temperature Unless Otherwise Specified) (Cont'd)

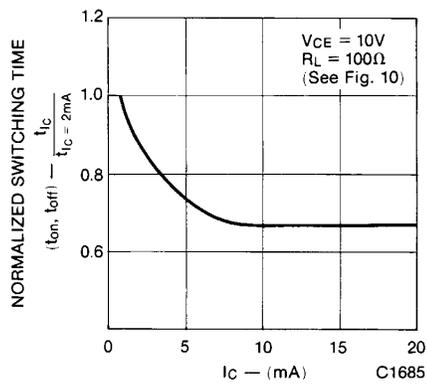


Fig. 9. Switching Time vs. IC

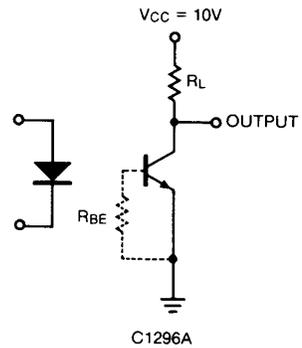


Fig. 10. Switching Time Test Circuit

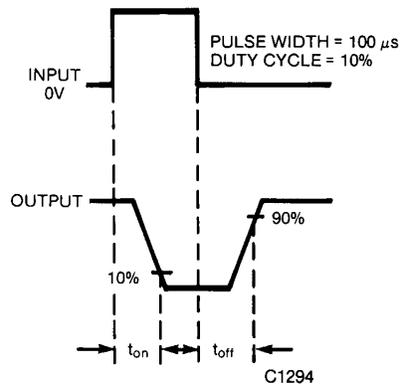


Fig. 11. Switching Time Waveforms



## PHOTOTRANSISTOR OPTOCOUPLEDERS

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2. A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.